

**In the Specification<sup>1</sup>:**

Please replace paragraph 1, page 27, with the following paragraph:

A1  
Hafnia films were grown with the precursors listed in Table I. Precursor solutions were prepared at 0.1M Hf in octane. Substrate of (100) Si was prepared with an SC1 treatment followed by dilute HF to remove any SiO<sub>2</sub> on the surface. The generic process conditions for the experiments are shown in Table II. Initially, films were grown at 550°C under three different reactive gas conditions: Ar, N<sub>2</sub>O and O<sub>2</sub>. Results described below indicated that N<sub>2</sub>O was the preferred ambient. A pressure-temperature matrix was performed for each precursor using the N<sub>2</sub>O ambient as shown in Figures 2A and 2B. Figures 2A and 2B show the process space experiments for TDEAHf and TDMAHf precursors, where the various experiments are identified as GXXX. At the end, a film targeting 50Å was grown from each precursor to be used for TEM examination of the interface with Si.

Please replace paragraph 1, page 30, with the following paragraph:

A2  
Silica films were grown with the silicon precursors listed in Table III, TDEASi and TDMASi. Precursor solutions were prepared at 0.1M Si in octane. Substrates of (100) Si were prepared with an SC1 treatment followed by dilute HF to remove any native SiO<sub>2</sub>. The generic process conditions for the experiments are shown in Table IV. Results from the growth of hafnia films encouraged us to center these initial experiments on growth in an N<sub>2</sub>O atmosphere although growth in O<sub>2</sub> or other oxidizer could be used at temperatures at or below 500°C. A limited pressure-temperature matrix was performed for each Si precursor using the N<sub>2</sub>O ambient as shown in Figure 7A and 7B, where the various experiments are identified as GXXX.

Please replace paragraph 3, page 31, with the following paragraph:

A3  
Growth rates of SiO<sub>2</sub> were less than 3Å/min under all conditions as shown in Figure 8 and Figure 9. There is some indication that the TDEASi may form silica films a little bit more readily,

<sup>1</sup> Applicants have provided a marked-up version of the amended claims in Appendix A, a marked up version of paragraph amendments in Appendix B and a clean set of amended paragraphs in Appendix C.